2022년 1월 25일(화), 10:45-12:00 Room F (스페이드 I, 6층)

## G. Device & Process Modeling, Simulation and Reliability 분과 [TF2-G] Logic Devices and Reliability

좌장: 홍성민 교수(GIST), 백록현 교수(POSTECH)

48. 88E ± ( (881), 44E ± ( (881)	
TF2-G-1 10:45-11:15	Knowledge-Based Neural Compact Model for Semiconductor Device Modeling Soogine Chong, Chanwoo Park, Ye Sle Cha, Chul-Heung Kim, and Hyunbo Cho Alsemy Inc.
TF2-G-2 11:15-11:30	Explicit Surface-Potential Based Compact Model of Negative-Capacitance FETs with MFIS for Accelerated SPICE Simulation Ju-Hyun Shim and Ji-Woon Yang Department of Electronics and Information Engineering, Korea University
TF2-G-3 11:30-11:45	Sensitivity Analysis of each Inner Spacer Thickness Variation in Sub 3-nm Node Silicon Nanosheet Field-Effect Transistors Sanguk Lee, Jun-Sik Yoon, Jinsu Jeong, Seunghwan Lee, Junjong Lee, Jaewan Lim, and Rock-Hyun Baek Department of Electrical Engineering, POSTECH
TF2-G-4 11:45-12:00	FDSOI-Based Polarity Gate-Less Reconfigurable FET  Dong Hyeok Lee <sup>1</sup> and Jiwon Chang <sup>2</sup> <sup>1</sup> Department of Materials Science & Engineering, Yonsei University, <sup>2</sup> Department of System Semiconductor Engineering, Yonsei University